

METHOD FOR DETECTING THE END POINT OF PLASMA ETCHING PROCESS BY USING MATRIX

ABSTRACT OF THE DISCLOSURE

5 A method for detecting the end point of plasma etching process by
using matrix comprises a step of detecting a beginning matrix including
emitting intensities and/or other plasma parameters of at least two
different plasma species during beginning etching process. Then, a step
of detecting an etching matrix is performed in which the etching matrix
10 includes emitting intensities and/or other plasma parameters of the at
least two different plasma species at the etching reaction. An end point
matrix is then computed by using the beginning as well as etching
matrices and compared to a reference end point matrix to decide whether
the end point is reached.